Form PTO-1449 (Modified)	Attorney Docket No.: FIS920030183US1	Serial No.: 10/605,108
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	Applicant: Dureseti Chidambarrao, et al.	
(Use several sheets if necessary) Page 1 of 1	Filing Date: September 9, 2003	Group: 2814

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINERS INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
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OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

LP			Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si *n*-MOSFETs", International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
			Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs", 2002 Symposium On VLSI Technology Digest of Technical Papers, IEEE, pp 98-99.
			Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress", International Electron Devices Meeting, 34.4.1, IEEE, September 1999.
			F. Ootsuka, et al., "A Highly Dense, High-Performance 130nm node CMOS Technology for Large Scale System-on-a-Chip Application", International Electron Devices Meeting, 23.5.1, IEEE, April 2000.
			Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design", International Electron Devices Meeting, 10.7.1, IEEE, April 2000.
			A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement", International Electron Devices Meeting, IEEE, March 2001.
			K. Ota, et al., "Novel Locally Strained Channel Technique for high Performance 55nm CMOS", International Electron Devices Meeting, 2.2.1, IEEE, February 2002.

EXAMINER	DATE CONSIDERED
Long Pham	~~5/30~~ 5/03/04

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. FIS920030183US1	SERIAL NO. 10/605,108
	APPLICANT: Dureseti Chidambarrao, et al.	
	FILING DATE: 9/9/03	GROUP: Unassigned

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
LP							
		6,406,973 B1	6/18/2002	Lee			
		6,281,532 B1	8/28/2001	Doyle et al.			
		5,683,934	11/4/97	Candelaria			
		6,368,931 B1	4/9/2002	Kuhn, et al.			
		5,310,446	5/10/94	Konishi et al.			
		4,853,076	8/1/89	Tsaur et al.			
		US 2002/0090791 A1	7/11/2002	Doyle et al.			
		US 2002/0074598 A1	6/20/2002	Doyle et al.			
		6,509,618 B2	1/21/03	Jan et al.			
		6,476,462 B2	11/5/2002	Shimizu et al.			
		6,362,082 B1	3/26/2002	Doyle et al.			
		6,228,694 B1	5/8/2001	Doyle et al.			
		5,565,697	10/15/96	Asakawa et al.			
		US 2003/0040158 A1	2/27/2003	Saitoh			
		US 2002/0086472 A1	7/4/2002	Roberds et al.			
		6,521,964 B1	2/18/2003	Jan et al.			
✓		6,506,652	01/14/03	Jan, et al.			

FOREIGN PATENT DOCUMENTS

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OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

EXAMINER	Long Pham	DATE CONSIDERED	5/3/04

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U.S. PATENT DOCUMENTS

EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
LP		5,081,513	1/14/1992	Jackson, et al.			
		3,602,841	8/31/1971	McGroddy			
		6,531,740	3/11/2003	Bosco, et al.			
		6,531,369	3/11/2003	Ozkan, et al.			
		6,501,121	12/31/2002	Yu, et al.			
		6,498,358	12/24/2002	Lach, et al.			
		6,493,497	12/10/2002	Ramdani, et al.			
		6,403,975	6/11/2002	Brunner, et al.			
		6,361,885	3/26/2002	Chou			
		6,255,169	7/3/2001	Li, et al.			
		6,246,095	6/12/2001	Brady, et al.			
		6,165,383	12/26/2000	Chou			
		6,133,071	10/17/2000	Nagai			
		6,046,464	4/4/2000	Schetzina			
✓		6,025,280	2/15/2000	Brady, et al.			

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EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
LP		5,940,736	8/17/1999	Brady, et al.			
		5,880,040	3/9/1999	Sun, et al.			
		5,861,651	1/19/1999	Brasen, et al.			
		5,679,965	10/21/1997	Schetzina			
		5,670,798	9/23/1997	Schetzina			
		5,561,302	10/1/1996	Candelaria			
		5,471,948	12/5/1995	Burroughes, et al.			
		5,459,346	10/17/1995	Asakawa, et al.			
		5,391,510	2/21/1995	Hsu, et al.			
		5,371,399	12/6/1994	Burroughes, et al.			
		5,108,843	4/28/1992	Ohtaka, et al.			
		5,060,030	10/22/1991	Hoke			
		4,958,213	9/18/1990	Eklund, et al.			
		4,665,415	5/12/1987	Esaki, et al.			
✓							

FOREIGN PATENT DOCUMENTS

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U.S. PATENT DOCUMENTS

EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
LP		5,989,978	11/23/1999	Peidous			
		6,284,626	9/4/2001	Kim			
		6,274,444	8/14/2001	Wang			
		6,261,964	7/17/2001	Wu, et al.			
		6,221,735	4/24/2001	Manley, et al.			
		6,117,722	9/12/2000	Wuu, et al.			
		6,107,143	8/22/2000	Park, et al.			
		6,090,684	7/18/2000	Ishitsuka, et al.			
		6,066,545	5/23/2000	Doshi, et al.			
		6,008,126	12/28/1999	Leedy			
		5,946,559	8/31/1999	Leedy			
		5,840,593	11/24/1998	Leedy			
		5,592,018	1/7/1997	Leedy			
		5,592,007	1/7/1997	Leedy			
✓		5,571,741	11/5/1996	Leedy			

FOREIGN PATENT DOCUMENTS

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REFERENCE DESIGNATION **U.S. PATENT DOCUMENTS**

EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
LP		5,557,122	9/17/1996	Shrivastava, et al.			
		5,354,695	10/11/1994	Leedy			
		5,134,085	7/28/1992	Gilgen, et al.			
		5,006,913	4/9/1991	Sugahara, et al.			
		4,952,524	8/28/1990	Lee, et al.			
		4,855,245	8/8/1989	Neppl, et al.			

FOREIGN PATENT DOCUMENTS

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INFORMATION DISCLOSURE CITATION

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Docket Number (Optional)	Application Number
FIS920030183US1	10/605,108
Applicant(s)	
Chidambarrao, Dureseti, et al.	
Filing Date	**Group Art Unit**
9/9/03	Unassigned

U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

LP		Novel Locally Strained Channel Technique for High Performance 55 nm CMOS K. Ota, et al. 2002 IEEE, 2.2.1-2.2.4 IEDM 27 Local Mechanical-Stress Contro; (LMC): A New Technique for CMOS-Performance Enhancement A. Shimizum. et al. 2001 IEEE, 19.4.1-19.4.4 IEDM 01-433
↓		Mechanical Stress Effect of Etch-Stop Nitride and its impact on Deep Submicron Design Shinya Ito, et al. 2000 IEEE, 10.7.1-10.7.4 IEDM 00-247 A Highly Dence, High-Performance 130nm node CMOS Technology for Large Scale System-on-a-Chip Applications F. Ootsuka, et al. 2000 IEEE, 23.5.1-23.5.4 IEDM 00-575

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INFORMATION DISCLOSURE CITATION

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Chidambarra , Dureseti, et al.	
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9/9/03	Unassigned

U.S. PATENT DOCUMENTS

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LP		NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress Gregory Scott, et al. 1999 IEEE, 34.4.1-24.4.4 IEDM 99-827 Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs Kern (Ken) Rim, et al. 1998 IEEE, 26.8.1-26.8.4 IEDM 98-707
LP		Characteristics and Device Design of Sub-100 nm Strained Si N - and PMOSFETs K. Rim, et al. 2002 IEEE, 98-99, 2002 Symposium On VLSI Technology Digest of Technical Papers

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